

PROTECTION PRODUCTS - MicroClamp™

Description

The μ Clamp™ series of TVS arrays are designed to protect sensitive electronics from damage or latch-up due to ESD, lightning, and other voltage-induced transient events. Each device will protect up to six lines operating at **3.3 volts**.

The μ Clamp™3306P is a solid-state device designed specifically for transient suppression. It is constructed using Semtech's proprietary EPD process technology. The EPD process provides low standoff voltages with significant reductions in leakage currents and capacitance over traditional pn junction processes. They offer desirable characteristics for board level protection including fast response time, low clamping voltage and no device degradation.

The μ Clamp3306P may be used to meet the immunity requirements of IEC 61000-4-2, level 4 (± 15 kV air, ± 8 kV contact discharge). It is packaged in an ultra small SLP1616P6 package with a low profile of only 0.58mm. The leads are spaced at a pitch of 0.5mm and are finished with lead-free NiPd. The small package makes it ideal for use in portable electronics such as cell phones, digital still cameras, and notebook computers.

Features

- ◆ Transient protection for data lines to **IEC 61000-4-2 (ESD) ± 15 kV (air), ± 8 kV (contact)**
IEC 61000-4-4 (EFT) 40A (tp = 5/50ns)
- ◆ Small package for use in portable electronics
- ◆ Protects Six I/O
- ◆ Working voltage: 3.3V
- ◆ Low leakage current
- ◆ Low operating and clamping voltages
- ◆ Solid-state silicon-avalanche technology

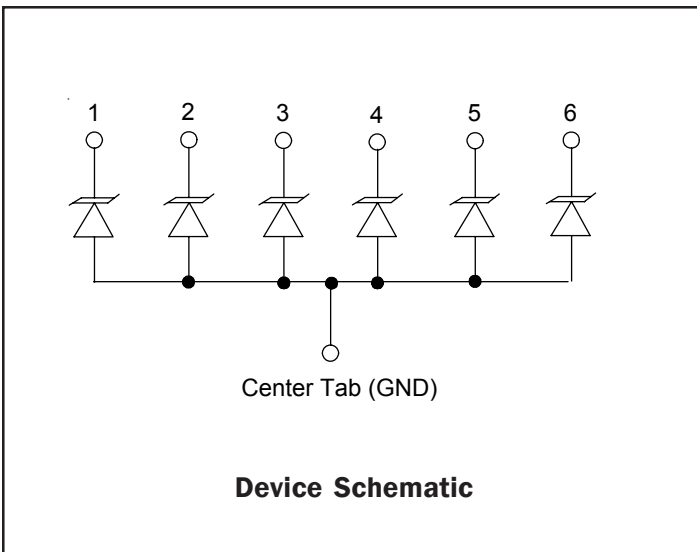
Mechanical Characteristics

- ◆ SLP1616P6 package
- ◆ RoHS/WEEE Compliant
- ◆ Nominal Dimensions: 1.6 x 1.6 x 0.58 mm
- ◆ Lead Pitch: 0.5mm
- ◆ Lead Finish: NiPd
- ◆ Marking : Orientation Mark and Marking Code
- ◆ Packaging : Tape and Reel per EIA 481

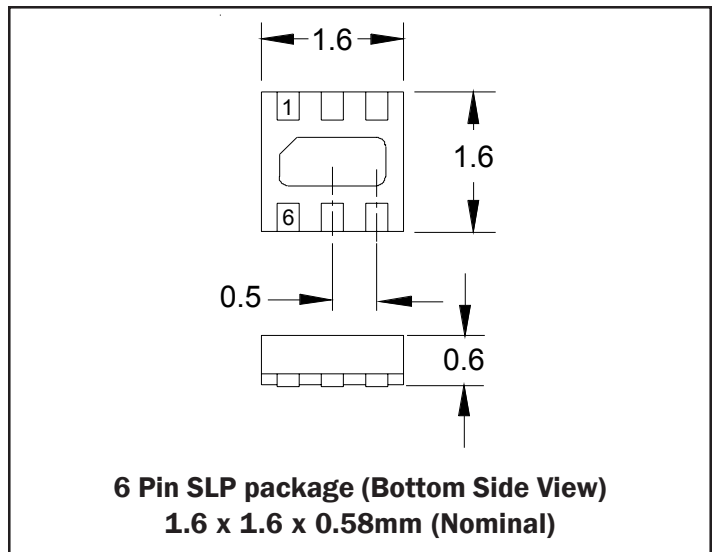
Applications

- ◆ Cellular handsets and accessories
- ◆ Notebooks and handhelds
- ◆ MP3 Players
- ◆ Digital cameras
- ◆ Portable instrumentation

Circuit Diagram



Package



PROTECTION PRODUCTS
Absolute Maximum Rating

Rating	Symbol	Value	Units
Peak Pulse Power (tp = 8/20μs)	P_{pk}	40	Watts
Maximum Peak Pulse Current (tp = 8/20μs)	I_{pp}	5	Amps
ESD per IEC 61000-4-2 (Air) ESD per IEC 61000-4-2 (Contact)	V_{pp}	+/- 20 +/- 15	kV
Operating Temperature	T_J	-55 to +125	°C
Storage Temperature	T_{STG}	-55 to +150	°C

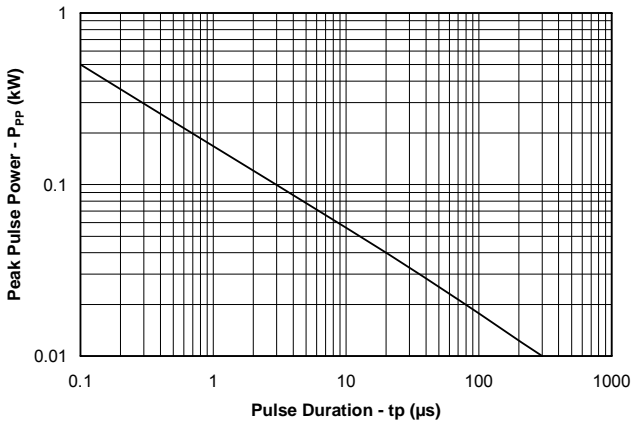
Electrical Characteristics (T=25°C)

Parameter	Symbol	Conditions	Minimum	Typical	Maximum	Units
Reverse Stand-Off Voltage	V_{RWM}				3.3	V
Punch-Through Voltage	V_{PT}	$I_{PT} = 2\mu A$	3.5			V
Snap-Back Voltage	V_{SB}	$I_{SB} = 50mA$	2.8			V
Reverse Leakage Current	I_R	$V_{RWM} = 3.3V$		0.05	0.5	μA
Clamping Voltage	V_C	$I_{pp} = 1A$, tp = 8/20μs Any I/O to Gnd			5.5	V
Clamping Voltage	V_C	$I_{pp} = 5A$, tp = 8/20μs Any I/O to Gnd			8.0	V
Reverse Clamping Voltage	V_{CR}	$I_{pp} = 1A$, tp = 8/20μs Any I/O to Gnd			2.4	V
Junction Capacitance	C_J	I/O pin to Gnd $V_R = 0V$, f = 1MHz		20	25	pF
		I/O pin to Gnd $V_R = 3.3V$, f = 1MHz		12		pF
		I/O pin to I/O pin $V_R = 0V$, f = 1MHz		10	12.5	pF
		I/O pin to I/O pin $V_R = 3.3V$, f = 1MHz		7.5		pF

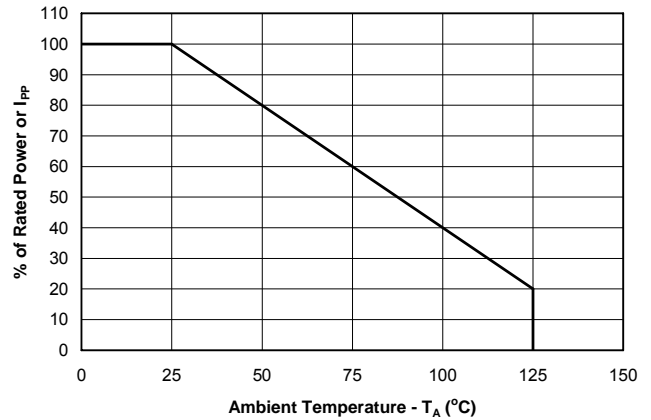
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Typical Characteristics

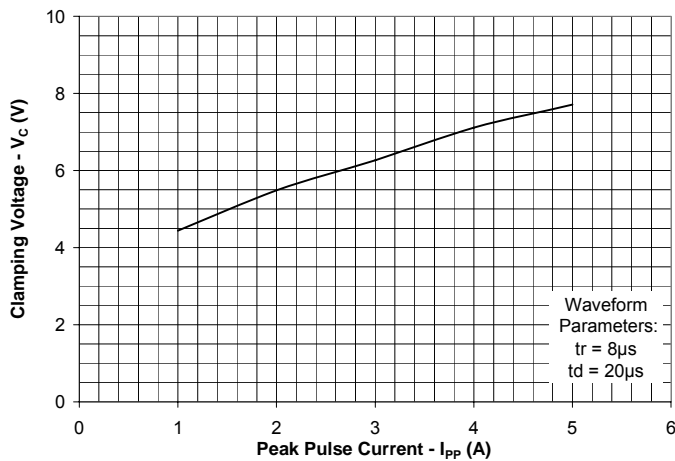
Non-Repetitive Peak Pulse Power vs. Pulse Time



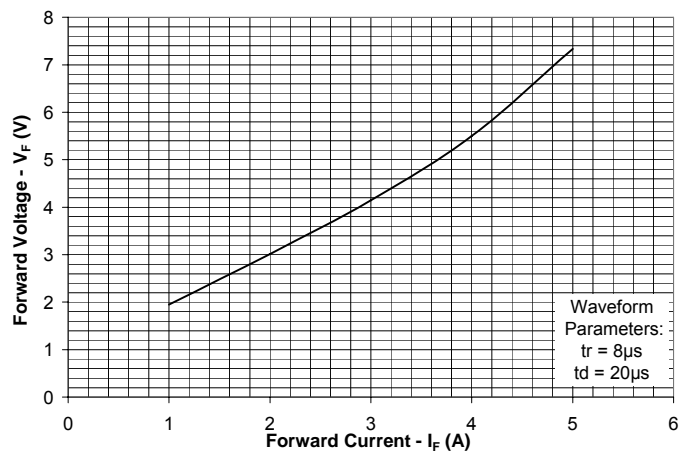
Power Derating Curve



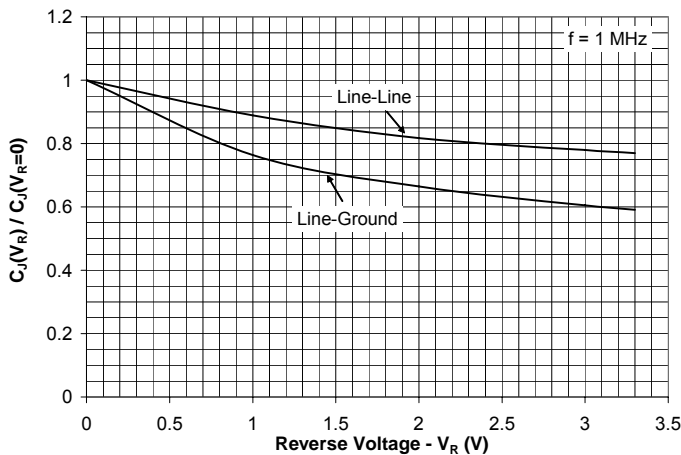
Clamping Voltage vs. Peak Pulse Current



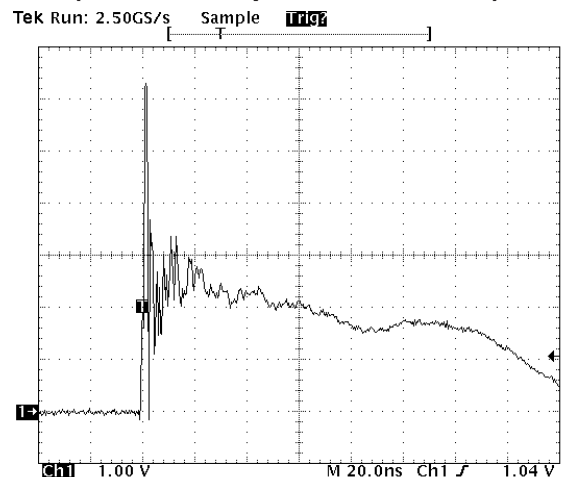
Forward Voltage vs. Forward Current

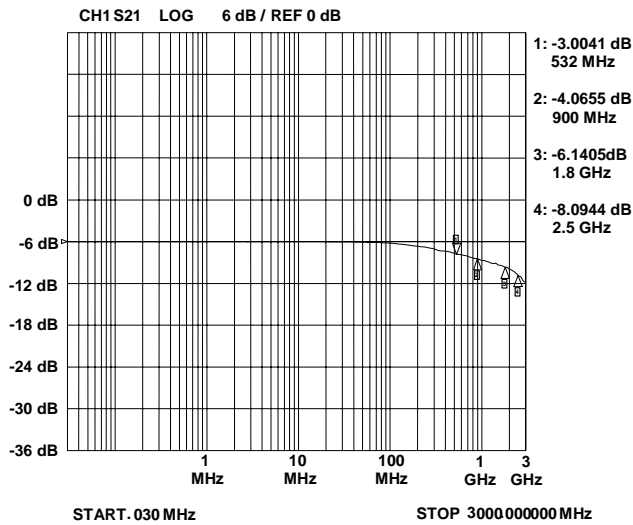
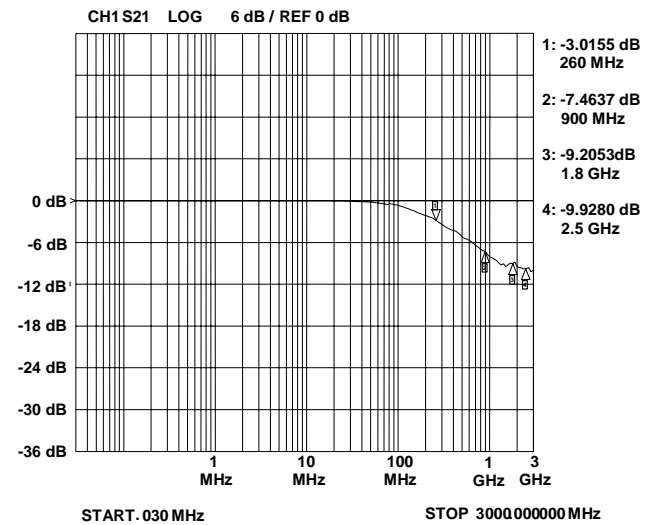
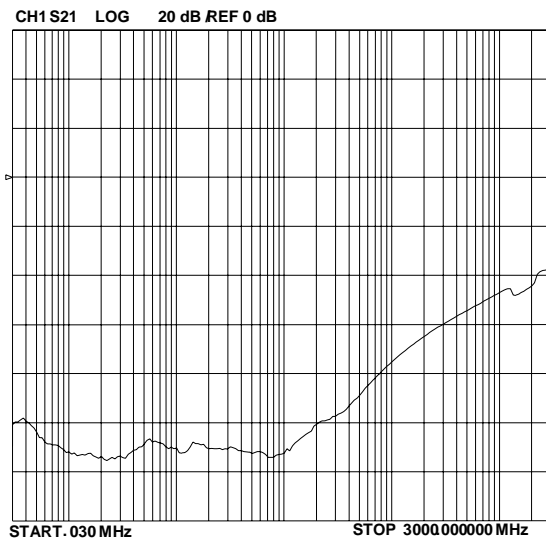


Normalized Capacitance vs. Reverse Voltage



ESD Clamping (8kV Contact per IEC 61000-4-2)



Insertion Loss S21 - LtoL (I/O to I/O)

Insertion Loss S21 -LtoG (I/O to Pin 2)

Crosstalk S21 (I/O to Pin 4)


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Applications Information

Device Connection Options

The μ Clamp3306P is designed to protect 6 signal lines with an operating voltage of 0 to 3.3V. It will present a high impedance to the protected line up to 3.3 volts. It will “turn on” when the line voltage exceeds 3.5 volts. The device is unidirectional and may be used on lines where the signal polarity is above ground.

Pins 1, 2, 3, 4, 5, and 6 are connected to I/O signals. The center tab is connected to system ground. All signal lines and ground should be made with the lowest impedance and inductance path as possible. This will improve signal quality of the lines and keep the clamping voltage as low as possible during a fast transient.

EPD TVS Characteristics

These devices are constructed using Semtech’s proprietary EPD technology. The structure of the EPD TVS is vastly different from the traditional pn-junction devices. At voltages below 5V, high leakage current and junction capacitance render conventional avalanche technology impractical for most applications. However, by utilizing the EPD technology, these devices can effectively operate at 3.3V while maintaining excellent electrical characteristics.

The EPD TVS employs a complex npnp structure in contrast to the pn structure normally found in traditional silicon-avalanche TVS diodes. The EPD mechanism is achieved by engineering the center region of the device such that the reverse biased junction does not avalanche, but will “punch-through” to a conducting state. This structure results in a device with superior DC electrical parameters at low voltages while maintaining the capability to absorb high transient currents.

Figure 1 - Circuit Diagram

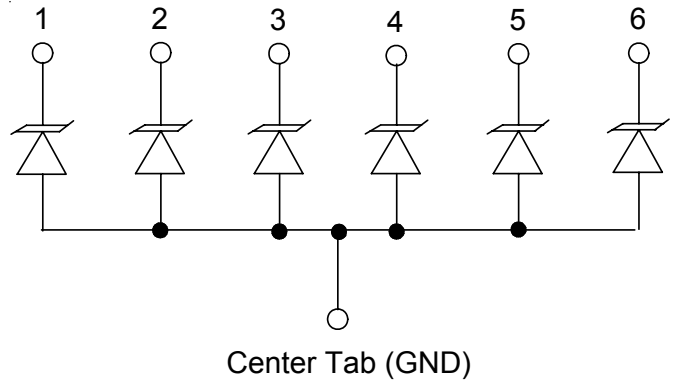


Figure 2 - Layout Example

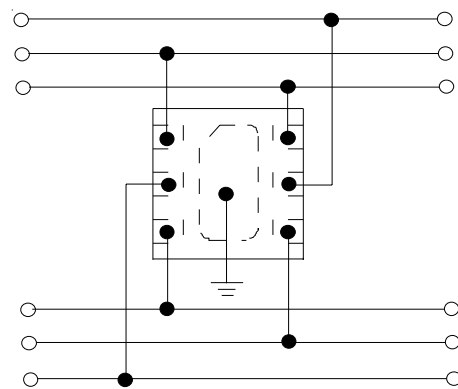
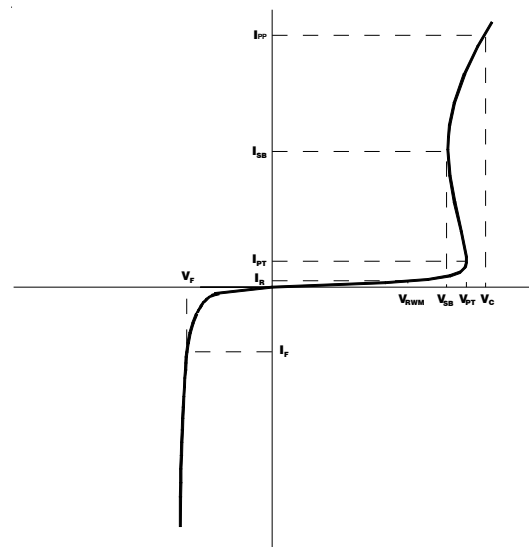
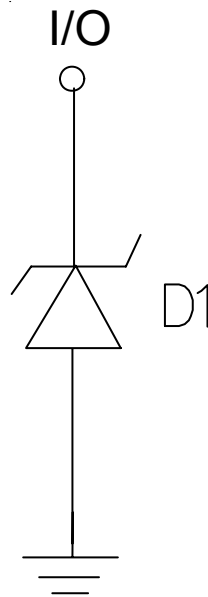


Figure 3 - EPD TVS IV Characteristic Curve

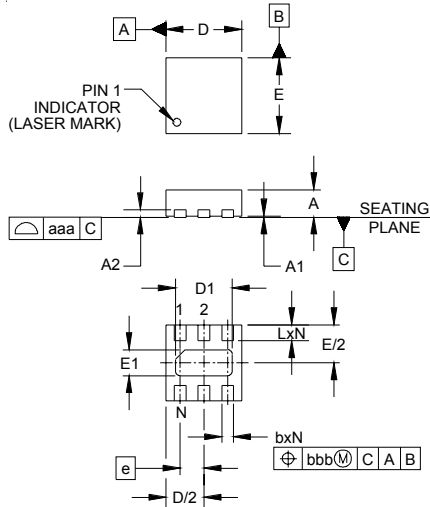


PROTECTION PRODUCTS
Applications Information - Spice Model

Figure 3 - μ Clamp3306P Spice Model

μClamp3306P Spice Parameters		
Parameter	Unit	D1 (TVS)
IS	Amp	2E-12
BV	Volt	20
VJ	Volt	0.57
RS	Ohm	1.444
IBV	Amp	1.0 E-3
CJO	Farad	20E-12
TT	sec	2.541E-9
M	--	0.236
N	--	1.1
EG	eV	1.11

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Outline Drawing - SLP1616P6

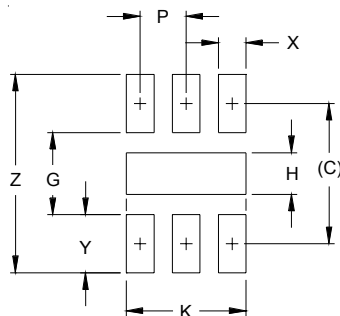


DIM	DIMENSIONS					
	INCHES			MILLIMETERS		
	MIN	NOM	MAX	MIN	NOM	MAX
A	.020	.023	.026	0.50	0.58	0.65
A1	0.00	.001	.002	0.00	0.03	0.05
A2		(.005)			(0.13)	
b	.008	.010	.012	0.20	0.25	0.30
D	.059	.063	.067	1.50	1.60	1.70
D1	.041	.047	.051	1.05	1.20	1.30
E	.059	.063	.067	1.50	1.60	1.70
E1	.010	.016	.020	0.25	0.40	0.50
e	.020 BSC			0.50 BSC		
L	.010	.013	.016	0.25	0.33	0.40
N	6			6		
aaa	.003			0.08		
bbb	.004			0.10		

NOTES:

1. CONTROLLING DIMENSIONS ARE IN MILLIMETERS (ANGLES IN DEGREES).
2. COPLANARITY APPLIES TO THE EXPOSED PAD AS WELL AS THE TERMINALS.

Land Pattern - SLP1616P6



DIM	DIMENSIONS	
	INCHES	MILLIMETERS
C	.060	1.52
G	.035	0.89
H	.018	0.45
K	.051	1.30
P	.020	0.50
X	.012	0.30
Y	.025	0.63
Z	.085	2.15

NOTES:

1. CONTROLLING DIMENSIONS ARE IN MILLIMETERS (ANGLES IN DEGREES).
2. THIS LAND PATTERN IS FOR REFERENCE PURPOSES ONLY. CONSULT YOUR MANUFACTURING GROUP TO ENSURE YOUR COMPANY'S MANUFACTURING GUIDELINES ARE MET.
3. THERMAL VIAS IN THE LAND PATTERN OF THE EXPOSED PAD SHALL BE CONNECTED TO A SYSTEM GROUND PLANE. FAILURE TO DO SO MAY COMPROMISE THE THERMAL AND/OR FUNCTIONAL PERFORMANCE OF THE DEVICE.